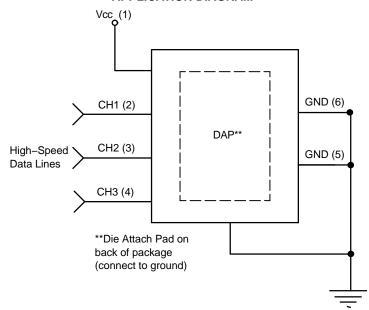
ESD7124

4-Channel Low Capacitance Dual-Voltage ESD and Surge Protection Array

Features

- 3 Channels of Low Voltage ESD Protection
- 1 Channel of High Voltage ESD Protection
- Provides ESD Protection to IEC61000-4-2 Level 4: ±25 kV Contact Discharge
- IEC 61000-4-5 (lighting)
- Low Channel Input Capacitance
- High Voltage Zener Diode Protects Supply Rail up to 100 A (8/20 μs)
- These Devices are Pb-Free and are RoHS Compliant

APPLICATION DIAGRAM





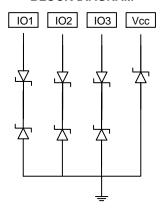
ON Semiconductor®

http://onsemi.com



UDFN-6 D4 SUFFIX CASE 517CS

BLOCK DIAGRAM



MARKING DIAGRAM



AD = Specific Device Code

M = Date Code

■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
ESD7124MUTBG	UDFN-6	3000/Tape &
	(Pb-Free)	Reel

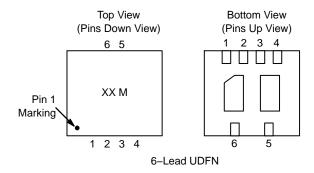
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ESD7124

Table 1. PIN DESCRIPTIONS

	4-Channel, 6-Lead, UDFN-8 Package						
Pin	Name	Туре	Description				
1	V _{CC}	HV V _{DD}	HV ESD Channel				
2	CH1	I/O	LV Low-capacitance ESD Channel				
3	CH2	I/O	LV Low-capacitance ESD Channel				
4	СНЗ	I/O	LV Low-capacitance ESD Channel				
5	GND		Ground				
6	6 GND		Ground				

PACKAGE / PINOUT DIAGRAMS



SPECIFICATIONS

Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
Operating Temperature Range	-55 to +125	°C
Storage Temperature Range	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 3. ELECTRICAL CHARACTERISTICS

	Reverse Working Voltage	Break Voltage	down Vbr (V)	Reverse Current Leakage Ir (μΑ)	Rdyn	Junction Capactance Cj(pF)	
	Vrwm (V)	at 1 mA		at Vrwm Ω		Vr = 0 V, f = 1 MHz	
Device Name	Max	Min	Тур	Max	Тур	Тур	Max
Pin2-4 (LV)	3.3	5.5	6.5	1	1	0.35	0.5
Pin1 (HV)	12	13.3	14	1			

		oltage Vc (V) x 20 μs		Ratings x 20 μs
	lpp = 1 A	lpp = 16 A	lpp (A)	Vc @ Max Ipp (V)
Device Name	Тур	Тур	Max	Max
Pin1 (HV)	15	16	100	27
Pin2-4 (LV)	9.5	1		

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Clamping Voltage TLP (Note 1) All Devices Pin2-4(LV)	V _C	$I_{PP} = \pm 8 \text{ A}$		16.8		V
See Figures 3 – 6		$I_{PP} = \pm 16 \text{ A}$ } IEC 61000-4-2 Level 4 equivalent ($\pm 8 \text{ kV Contact}, \pm 15 \text{ kV Air}$)		24.9		

^{1.} ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50 \ \Omega$, $t_p = 100 \ ns$, $t_r = 4 \ ns$, averaging window; $t_1 = 30 \ ns$ to $t_2 = 60 \ ns$.

ESD7124

TYPICAL CHARACTERISTICS

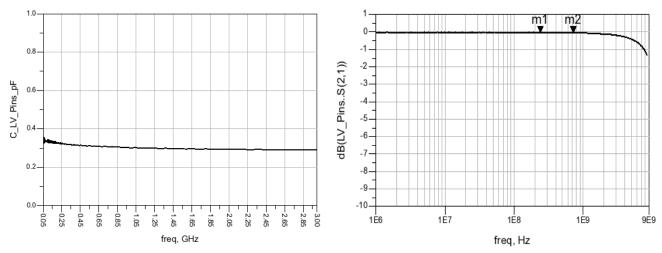


Figure 1. Capacitance Over Frequency

Figure 2. Insertion Loss

Interface	Data Rate (Mb/s)	Fundamental Frequency (MHz)	3 rd Harmonic Frequency (MHz)	ESD7124 Insertion Loss (dB)
USB 2.0	480	240 (m1)	720 (m2)	m1 = 0.031 m2 = 0.047

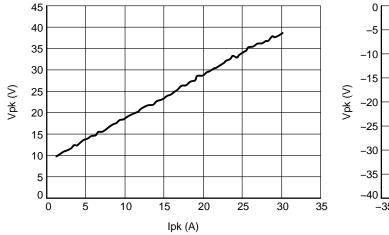


Figure 3. Positive TLP I-V Curve

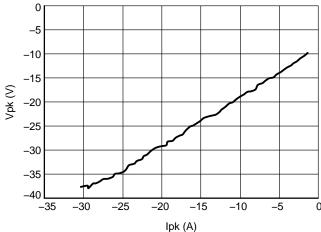


Figure 4. Negative TLP I-V Curve

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 5. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 6 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels. For more information on TLP measurements and how to interpret them please refer to AND9007/D.

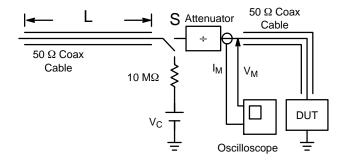


Figure 5. Simplified Schematic of a Typical TLP System

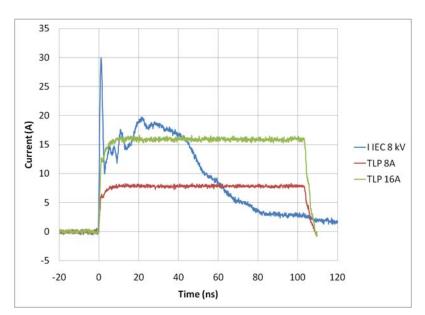


Figure 6. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms



C SEATING PLANE

С

□ 0.10

e1

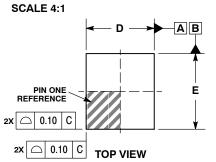
BOTTOM VIEW

0.10 C

e/2

e2

DATE 30 APR 2013



DETAIL B

SIDE VIEW

2X D2 -

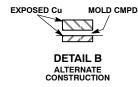
0.05 С

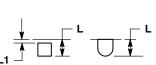
0.05 C

DETAIL A

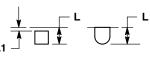
e1/2

NOTE 4

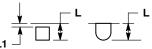




DETAIL A

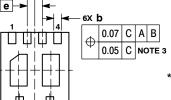






ALTERNATE CONSTRUCTIONS

0.07 C A B 0.05 C NOTE 3



SUPPLEMENTAL **BOTTOM VIEW**

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- 714.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION 6 APPLIES TO PLATED TERMINALS
 AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
 COPLANARITY APPLIES TO THE EXPOSED PAD
- AS WELL AS THE TERMINALS.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
A3	0.12	REF			
b	0.15	0.25			
D	1.80	BSC			
D2	0.35	0.55			
E	2.00	BSC			
E2	0.74	0.94			
е	0.40	BSC			
e1	0.80	BSC			
e2	0.95	BSC			
L	0.20	0.40			
11		0.15			

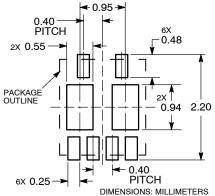
GENERIC MARKING DIAGRAM*



XX = Specific Device Code = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present.

RECOMMENDED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	UDFN6 1.8X2, 0.4P		PAGE 1 OF 1	

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